

Common Source

ARF468AG
ARF468BG

RF POWER MOSFETS

N-CHANNEL ENHANCEMENT MODE

150V 300W 45MHz

The ARF468A and ARF468B comprise a symmetric pair of common source RF power transistors designed for push-pull scientific, commercial, medical and industrial RF power amplifier applications up to 45 MHz. They have been optimized for both linear and high efficiency classes of operation.

- **Specified 150 Volt, 40.68 MHz Characteristics:**
 - Output Power = 300 Watts.**
 - Gain = 15dB (Class AB)**
 - Efficiency = 75% (Class C)**
- **Low Cost Common Source RF Package.**
- **Low V_{th} thermal coefficient.**
- **Low Thermal Resistance.**
- **Optimized SOA for Superior Ruggedness.**

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	Ratings	UNIT
V _{DSS}	Drain-Source Voltage	500	Volts
V _{DGO}	Drain-Gate Voltage	500	
I _D	Continuous Drain Current @ T _C = 25°C	22	Amps
V _{GS}	Gate-Source Voltage	±30	Volts
P _D	Total Power Dissipation @ T _C = 25°C	300	Watts
R _{θJC}	Junction to Case	0.35	°C/W
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T _L	Lead Temperature: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage (V _{GS} = 0V, I _D = 250 μA)	500			Volts
R _{DS(ON)}	Drain-Source On-State Resistance ^① (V _{GS} = 10V, I _D = 11A)			0.3	ohms
I _{DSS}	Zero Gate Voltage Drain Current (V _{DS} = 500V, V _{GS} = 0V)			25	μA
	Zero Gate Voltage Drain Current (V _{DS} = 400V, V _{GS} = 0V, T _C = 125°C)			250	
I _{GSS}	Gate-Source Leakage Current (V _{GS} = ±30V, V _{DS} = 0V)			±100	nA
g _{fs}	Forward Transconductance (V _{DS} = 25V, I _D = 11A)	5	8	9	mhos
V _{GS(TH)}	Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1mA)	2.5	4	5	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Microsemi Website - <http://www.microsemi.com>

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 150V$ $f = 1\text{ MHz}$		2230		
C_{oss}	Output Capacitance			230		pF
C_{rss}	Reverse Transfer Capacitance			105		

FUNCTIONAL CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
G_{PS}	Common Source Amplifier Power Gain	$f = 40.68\text{ MHz}$	14	15		dB
η	Drain Efficiency	$V_{GS} = 2.5V$ $V_{DD} = 150V$	70	75		%
Ψ	Electrical Ruggedness VSWR 10:1	$P_{out} = 300W$	No Degradation in Output Power			

① Pulse Test: Pulse width < 380μS, Duty Cycle < 2%

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TYPICAL PERFORMANCE CURVES

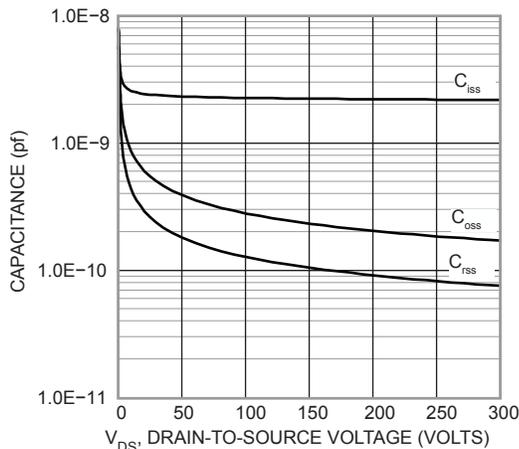


Figure 1, Typical Capacitance vs. Drain-to-Source Voltage

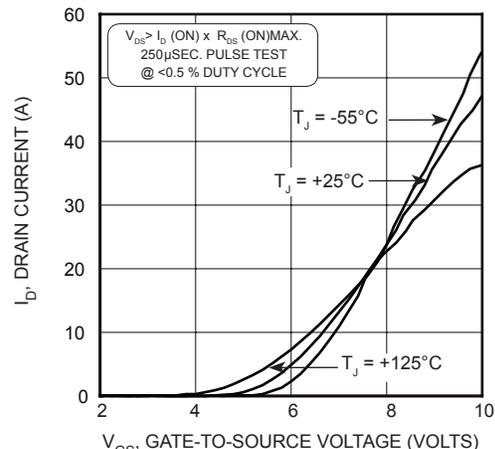


Figure 2, Typical Transfer Characteristics

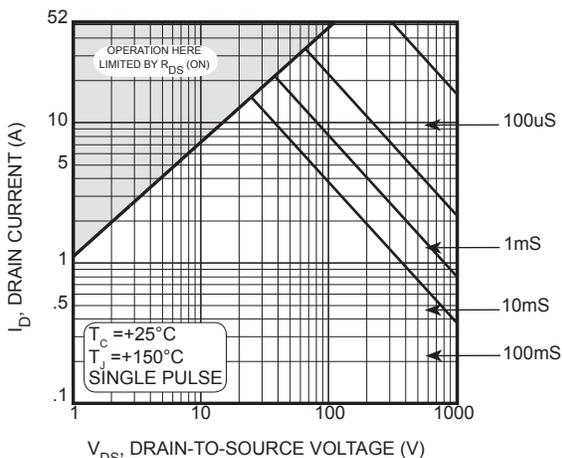


Figure 3, Typical Maximum Safe Operating Area

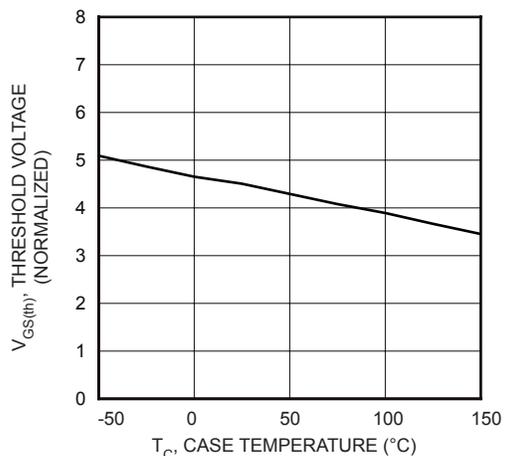


Figure 4, Typical Threshold Voltage vs Temperature

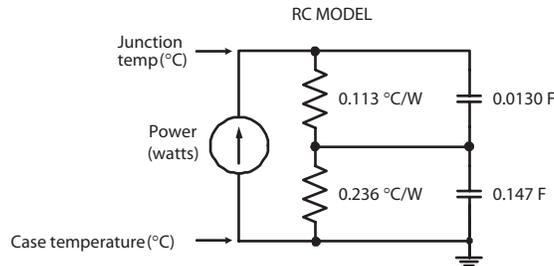
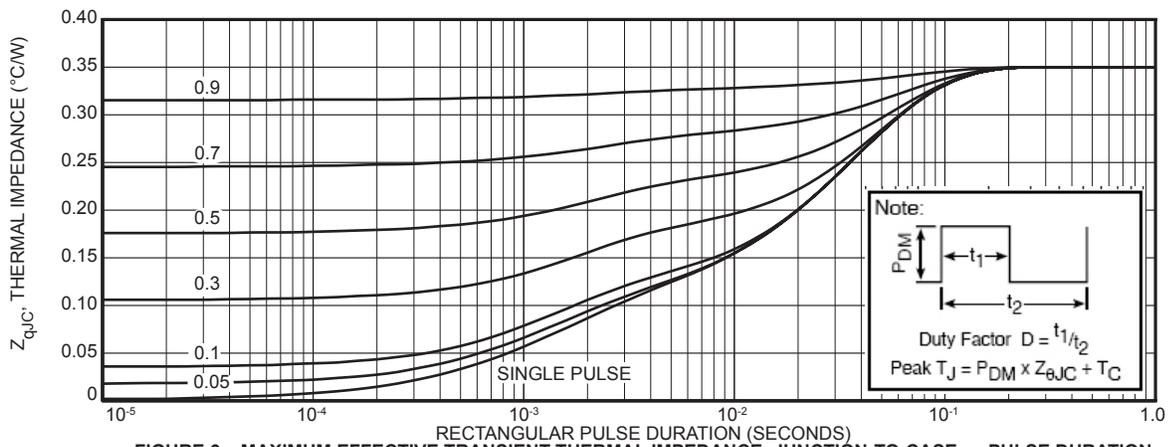
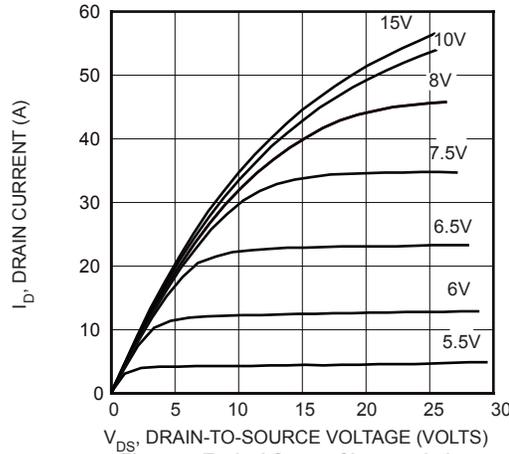
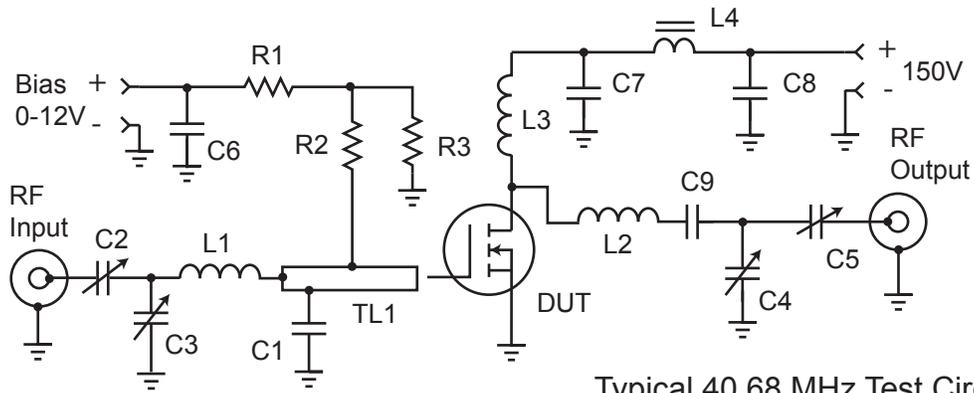


Figure 6b, TRANSIENT THERMAL IMPEDANCE

Table 1 - Typical Class AB Large Signal Input - Output Impedance

Freq. (MHz)	Z _{in} (Ω)	Z _{OL} (Ω)
2.0	18 - j 10.5	21 - j 1.4
13.5	2.7 - j 4.6	17.5 - j 7.8
27.1	1.8 - j 1.6	11.7 - j 10.4
40.7	1.7 - j 0.2	7.7 - j 10

Z_{IN} - Gate shunted with 25Ω I_{dg} = 0
 Z_{OL} - Conjugate of optimum load for 300 Watts output at V_{dd}=125V



Typical 40.68 MHz Test Circuit

C1 -- 2200pF ATC 700B

C2-C5 -- Arco 465 Mica trimmer

C6-C8 -- .1 μ F 500V ceramic chip

C9 -- 3x 2200 pF 500V chips COG

L1 -- 4t #22 AWG .25"ID .25" L ~87nH

L2 -- 5t #16 AWG .312" ID .35" L ~176nH

L3 -- 10t #24 AWG .25"ID ~.5 μ H

L4 -- VK200-4B ferrite choke 3 μ H

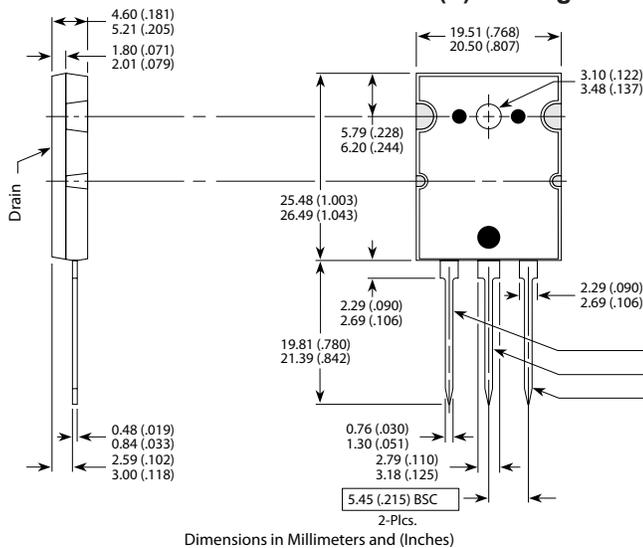
R1- R3 -- 1k Ω 0.5 Ω Carbon

TL1 -- 34 Ω t-line 0.175" x 1"

C1 .45" from gate pin.

PCB -- 0.062" FR4, Er=4.7

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)

NOTE: These two parts comprise a symmetric pair of RF power transistors and meet the same electrical specifications. The device pin-outs are the mirror image of each other to allow ease of use as a push-pull pair.

Device	
ARF - A	ARF - B
Gate	Drain
Source	Source
Drain	Gate

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